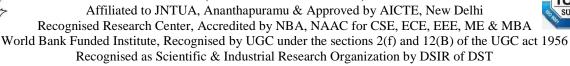


MADANAPALLE INSTITUTE OF TECHMOLOGY & SCIENCE (UCG-AUTONOMOUS)



Department of Electronics & Communication Engineering

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Report on

International Seminar on Recent Advances in Nonvolatile Memory for High-end Applications

13.03.2021



Report Submitted by: Dr. Sankar Prasad Bag & Dr. Tasher Ali Sheikh, Assistant Professor, Dept. of ECE, Department of Electronics and Communication Engineering

No. of Participants – 146

The resource person was: **Dr. Sreekanth Ginnaram** (Post-doctoral Research Fellow) from National Chung Hsing University, Taiwan, in the Dept. of Materials Science and Engineering and **Dr. Pranab Kumar Sarkar** (Assistant Professor) & HoD(i/c) Dept. of Applied Science and Humanities, Triguna Sen School of Technology, Assam University (A Central University) Silchar, Assam, India.

The department of Electronics and Communication Engineering, MITS, Madanapallle organized a one-day International Seminar on "Recent Advances in Nonvolatile Memory for High-end Applications". Dr. Sreekanth Ginnaram (Post-doctoral Research Fellow) from National Chung Hsing University, Taiwan, in the Dept. of Materials Science and Engineering presented this Seminar on 13/03/2021 from 10 am to 12 pm. He received Ph.D. from Chang Gung University (CGU), Taiwan, and M. Tech. from IIT Kharagpur, in the domain of Electronics Engineering.

And **Dr. Pranab Kumar Sarkar** (Assistant Professor) & HoD(i/c) from the Dept. of Applied Science and Humanities, Triguna Sen School of Technology, Assam University (A Central University) Silchar, Assam, India presented this Seminar on 13/03/2021 from 2 pm to 4 pm. Dr Sankar Prasad Bag and Dr. Tasher Ali Sheikh, Assistant Professor in the Department of ECE, MITS Madanapalle coordinate this event. The Chairperson of this event was Prof. (Dr.) C. Yuvaraj, Principal of MITS and Convener for the event was Dr S. Rajasekaran, HoD, Dept. of ECE, MITS, Madanapalle.

In the first session of this seminar **Dr. Sreekanth** was enlighten with the fundamentals of Nonvolatile Memory (NVM) Devices, Fundamentals and potential features of oxygen vacancy and conductive bridge random access memory devices (OXRAM and CBRAM) and its applications. In the second session **Dr. Sarkar** was given insights on Synaptic study in lead-free inorganic perovskite based flexible memrsitive device for neuromorphic systems.